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ARTICLE TYPE

Mediator-Free Direct Z-scheme Photocatalytic System: BiVO₄/g-C₃N₄ Organic-Inorganic Hybrid Photocatalyst with Highly Efficient Visible-Light-Induced Photocatalytic Activity

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We disclose the fabrication of a mediator-free direct Z-scheme photocatalyst system BiVO₄/g-C₃N₄ by using a mixed-calcination method based on more reliable interfacial interaction. The facet coupling occurred between the g-C₃N₄ (002) and BiVO₄ (121) was revealed by X-ray diffraction (XRD), X-ray photoelectron spectroscopy (XPS) and transmission electron microscope (TEM). The crystal structure and optical property of the as-prepared samples have also been characterized by fourier-transform infrared (FTIR), scanning electron microscopy (SEM) and UV-vis diffuse reflectance spectra (DRS) in details. The photocatalytic experiments indicated that the BiVO₄/g-C₃N₄ composite photocatalysts display a significantly enhanced photocatalytic activity pertaining to RhB degradation and photocurrent generation (PC) compared to the pristine BiVO₄ and g-C₃N₄. This remarkably improved photocatalytic performance should be attributed to the fabrication of a direct Z-scheme system of BiVO₄/g-C₃N₄, which can result in a more efficient separation of photoinduced charge carriers than band-band transfer, thus endowing it with the much more powerful oxidation and reduction capability, as confirmed by the photoluminescence (PL) spectra and electrochemical impedance spectra (EIS). The Z-scheme mechanism of BiVO₄/g-C₃N₄ heterostructure was verified by a series of combined techniques, including the active species trapping experiments, NBT transformation and terephthalic acid photoluminescence probing technique (TA-PL) over BiVO₄/g-C₃N₄ composites and the pristine samples. The present work not only furthered the understanding of mediator-free Z-scheme photocatalysis, but also shed new light on the design of heterostructural photocatalysts with high-performance.

1. Introduction

As a green and potential technology, semiconductor photocatalysis plays a vital role in the aspects of environmental protection and solar energy conversion.¹⁻⁷ Numerous attention have been paid toward the design of novel visible-light-responsive photocatalysts so as to maximize the utilization of the natural sunlight in the visible region ($\lambda > 420$ nm), which accounts for the largest proportion of the solar spectrum. Construction of heterostructures between two semiconductors is considered to be an effective method to promote the photocatalytic activity. Nowadays, the Z-scheme principled photocatalyst has attracted considerable attention due to its much stronger redox capacity than band-band transfer photocatalyst. The more negative CB and more positive VB potentials in Z-scheme photocatalyst separately endow the photogenerated electrons and holes with strong reduction and oxidation ability, thereby exhibiting significantly improved photocatalytic performance than the single component.^{8,9} For instance, the photocatalytic activity through the direct Z-scheme principle transfer is obviously higher than that by band-band transfer

mechanism in the visible-light-responsive Ag@AgBr/g-C₃N₄ composite photocatalyst.⁶ Other Z-scheme photocatalysts also largely prolong the lifetime of photoexcited carriers and exhibit highly enhanced photocatalytic activity than the two individuals. The Z-scheme systems are usually obtained by coupling two different photocatalysts combined with an appropriate intermediate or mediator (e.g. noble metals Ag and Au),¹⁰⁻¹³ which suffer from many drawbacks, such as low stability, high cost, etc. Compared with the mediator-containing ternary Z-scheme system, the mediator-free direct Z-scheme photocatalytic system only consisting of two components exhibits high stability, economic feasibility, etc, thus possessing the more promising practical application.¹⁴⁻¹⁷

As a promising candidate photocatalyst for organic pollutant removal and hydrogen production, graphite-like carbon nitride (g-C₃N₄) exhibits relatively high photocatalytic activity under visible-light irradiation due to its rapid separation of photoinduced charge carriers.¹⁸⁻²⁰ The very negative conduction band (-1.13 eV) of g-C₃N₄ enables a strong reduction power of the electrons (e⁻) in the conduction band (CB). Nevertheless,

there are still some shortcomings for the g-C₃N₄ utilization in photocatalysis process, such as the limited visible-light absorption below 450 nm, and small specific surface area.^{21,22} Recently, continuous efforts have been made to improve the photocatalytic performance of g-C₃N₄. Among which, combining g-C₃N₄ with other appropriate semiconductors to construct heterostructures can effectively promote the separation rate of photoexcited charge carriers. BiVO₄ is a visible-light-responsive photocatalyst with a narrow band gap of 2.40 eV, which has been admitted as a potential visible-light photocatalyst.²³⁻²⁵ However, the photogenerated e⁻ and h⁺ can be quickly decay via recombination,²⁶ resulting in relatively low photocatalytic activity of BiVO₄. Therefore, it limits the practical applications of BiVO₄ in photocatalytic degradation of pollutants. Consequently, it is an urgent strategy to enhance the efficiency of charge carriers separation rate and improve the visible-light photocatalytic activity of BiVO₄.

After energy level analysis, we found that the gap between the CB of g-C₃N₄ and the CB of BiVO₄ is much larger than that between the CB of BiVO₄ and the VB of g-C₃N₄. It may lead to that the photoinduced electrons in the CB of BiVO₄ transfer to the VB of g-C₃N₄ rapidly, which leaves rich electrons in the CB of g-C₃N₄ and holes in the VB of BiVO₄ to participate in the redox process, thus may resulting in a mediator-free direct Z-scheme photocatalytic system. Herein, we successfully prepared the direct Z-scheme photocatalyst system of BiVO₄/g-C₃N₄ by employing a mixed-calcination method, which may provide a more strong and reliable interfacial interaction between g-C₃N₄ and BiVO₄. The coupling between g-C₃N₄ and BiVO₄ happens on the (002) and (121) facets of g-C₃N₄ and BiVO₄, respectively. The photochemical activity of the BiVO₄/g-C₃N₄ was monitored via photocatalytic decomposition of the Rhodamine B (RhB) and photocurrent generation under visible-light irradiation ($\lambda > 420$ nm). The direct Z-scheme system of BiVO₄/g-C₃N₄ leads to a high efficiency separation of photogenerated electrons and holes, thus a highly improved photocatalytic activity. It was demonstrated by the active species trapping experiments, NBT transformation and terephthalic acid photoluminescence probing technique (TA-PL). It will be a generalized strategy to design other mediator-free direct Z-scheme photocatalysts with high-performance.

2. Experimental Section

2.1 Synthesis of heterostructured BiVO₄/g-C₃N₄ photocatalyst

The chemicals used in this study were of analytical grade without further purification. The g-C₃N₄ was synthesized via a calcination treatment of 5 g melamine in a corundum crucible without a cover in nitrogen.^{23,26} The crucible containing melamine was put into tube furnace and heated at 520°C for 4h. After cooling to room temperature, the yellow g-C₃N₄ product was obtained.

Pure BiVO₄ was prepared by a hydrothermal method as following. First of all, 0.005 mol of Bi(NO₃)₃•5H₂O was completely dissolved in 20 mL of HNO₃ (2 M) to form solution A. Second, 0.005 mol of NH₄VO₃ was dissolved in 10 mL of 2 M NaOH solution to form solution B. Then, solution B was dropwise added into solution A to form a yellow mixture

suspension. NaOH solution (1 M) was used to adjust the pH value to 7 of the obtained suspension and following by 30 min vigorously stirring. Then, move the resultant mixture to a 100 mL Teflon-lined stainless steel autoclave. The sealed autoclave was maintained at 180 °C for 12 h and afterwards cooling to room temperature naturally. After that, a yellow BiVO₄ powder was obtained with centrifugation, washed with water repeatedly, and finally dried in a vacuum oven.

The BiVO₄/g-C₃N₄ composites were obtained according to the following procedure. In a typical synthesis of BiVO₄/g-C₃N₄ with the molar ratio 1:9, 0.009 mol of g-C₃N₄ and 0.001 mol of BiVO₄ were mixed and ground thoroughly for 5 min. After that, the mixture was calcined at 400°C for 4 h to obtain the 1:9 BiVO₄/g-C₃N₄ photocatalyst. Other BiVO₄/g-C₃N₄ photocatalysts (2:8, 3:7, 4:6, 5:5 BiVO₄/g-C₃N₄) were prepared by the same processes, only the molar ratio of BiVO₄ to g-C₃N₄ were different. The pristine BiVO₄ and g-C₃N₄ were handled by the same method to ensure that they are under the same conditions.

2.2 Characterization

X-ray diffraction (XRD) analysis was employed to evaluate the phase structure of the as-prepared photocatalysts on a XRD-3 powder diffraction instrument with monochromatized Cu K α radiation ($\lambda = 1.5406$ nm) at a setting of 40 kV and 40 mA, and the scanning rate and range were 0.02° (2 θ)/s and 10-70°, respectively. A Bruker spectrometer was used to achieve the fourier-transform infrared (FTIR) spectra at a frequency range of 4000-500 cm⁻¹. Scanning electron microscopy (SEM) on a FEI Quanta 250 FEG instrument was applied to examine the general morphology of the photocatalysts. And a S-4300 transmission electron microscope (TEM, Hitachi) was employed to obtain the morphology and microstructure. The specific surface area was collected through Brumauer-Emmett-Teller (BET) method by N₂ adsorption (ASAP 2460, Micromeritics, USA). UV-vis diffuse reflectance spectra (DRS) of the samples were recorded on a Cary 5000 (America Varian) spectrophotometer. The surface properties of the photocatalysts were obtained by X-ray photoelectron spectroscopy (XPS) on a Thermo ESCALAB 250 instrument (USA) operating at 150 W with Al K α X-ray irradiation. The photoluminescence (PL) spectra were measured on a Hitachi F-4600 fluorescence spectrophotometer to investigate the recombination rate of electrons and holes.

2.3 Photocatalytic evaluation

As a common organic pollutant, RhB was employed to evaluate the photocatalytic activities of the as-prepared photocatalysts under visible-light ($\lambda > 420$ nm) degradation illuminated by a 500 W xenon lamp. 50 mg of the powder photocatalysts were dropped into quartz tubes which were containing 50 mL RhB solution (1 $\times 10^{-5}$ mol/L), respectively. Then, the above solution was ultrasonic dispersion for 10 min and stirred for 30 min in dark to achieve an adsorption-desorption equilibrium between the photocatalyst powder and RhB. Turn on the light and the photocatalytic reaction systems were exposed to visible light irradiation. At the same intervals, 3 mL of the mixture were taken out to centrifuge tubes, and the catalysts were removed out of the suspensions (4500 r/min, 5 min). The centrifuged solution was analyzed by recording the maximum absorption band (554 nm)

and UV-vis spectra were recorded by Shimadzu UV-5500PC spectrophotometer (produced by Shanghai Wuxiang Company).

2.4 Active species trapping and $\bullet\text{O}_2^-$ and $\bullet\text{OH}$ quantification experiments

Tert-butyl alcohol (TBA), 1, 4-benzoquinone (BQ) and disodium ethylenediaminetetraacetate (EDTA) were added in order to investigate the main active species, such as hydroxyl radicals ($\bullet\text{OH}$), superoxide radical ($\bullet\text{O}_2^-$) and holes (h^+) produced during the photoreaction process.^{10,27,28} NBT¹⁷ (2.5×10^{-5} mol/L) was used to detect the amount of $\bullet\text{O}_2^-$ generated from g- C_3N_4 , BiVO₄, 3:7 BiVO₄/g- C_3N_4 and mechanically mixed 3:7 BiVO₄/g- C_3N_4 . The production of $\bullet\text{O}_2^-$ was quantitatively analyzed by detecting the concentration of NBT with Shimadzu UV-5500PC spectrophotometer. To determine the amount of $\bullet\text{OH}$ producing from g- C_3N_4 , BiVO₄, 3:7 BiVO₄/g- C_3N_4 and mechanically mixed 3:7 BiVO₄/g- C_3N_4 , TA^{29,30} (5×10^{-4} M in a 2×10^{-3} M NaOH solution) was used as a probe molecule to react with $\bullet\text{OH}$ generating a highly fluorescent product 2-hydroxyterephthalic acid, whose concentration can reflect the yield of $\bullet\text{OH}$ measured by a Hitachi F-4600 fluorescence spectrophotometer.

2.5 Photoelectrochemical measurements experiments

The electrochemical experiments, including photocurrent response and electrochemical impedance spectra (EIS) of the samples as visible-light on and off, were conducted on a CHI660C electrochemical workstation (Chenhua Instrument Corporation, Shanghai). The BiVO₄/g- C_3N_4 film electrodes on ITO served as the working electrode, while a carbon electrode and a platinum saturated calomel electrode (SCE) were employed as the counter electrode and reference electrode, respectively. A xenon lamp with a power of 500 W acted as visible-light source, and 0.1 M Na₂SO₄ was used as the supporting electrolyte. The working voltage of the BiVO₄/g- C_3N_4 electrode was 0 V. And the whole process of the measurement was conducted in air at room temperature.

3. Results and discussion

3.1. Characterization

XRD analysis was applied to survey and evaluate the phase structure of the samples. Fig. 1a shows the XRD patterns of g- C_3N_4 , BiVO₄ and BiVO₄/g- C_3N_4 with different molar ratios. For the pure g- C_3N_4 , it can be clearly seen that the two distinct diffraction peaks at 27.40° and 13.04° correspond to the (002) and (100) diffraction planes, respectively, revealing that the diffraction peaks of g- C_3N_4 were in good agreement with the tetragonal phase of g- C_3N_4 (JCPDS 87-1526).^{31,32} Pure BiVO₄ shows a series of narrow and sharp diffraction peaks, which can be identified as the monoclinic phase of BiVO₄ (JCPDS 14-0688).^{33,34} For BiVO₄/g- C_3N_4 samples, it can be observed that the characteristic peaks of g- C_3N_4 gradually appeared with the increase of the g- C_3N_4 content. Thus, the XRD patterns of BiVO₄/g- C_3N_4 samples demonstrated that the characteristic diffraction peaks consisted of both g- C_3N_4 and BiVO₄, reflecting existence of the two phases.

Fig. 1b shows the FTIR spectra of g- C_3N_4 , BiVO₄ and BiVO₄/g- C_3N_4 composites. In the spectrum of pure BiVO₄, the

peak at 742 cm⁻¹ can be attributed to the ν_3 asymmetric stretching vibration of the VO₄ unit ν_3 (VO₄), and that at 842 cm⁻¹ corresponded to the ν_1 symmetric stretching vibration of the VO₄ unit ν_1 (VO₄).^{35,36} The absorption bands of pure g- C_3N_4 sample indicated the typical molecular structure of g- C_3N_4 . The intense bands in 900–1200 cm⁻¹ region can be assigned to the typical stretching modes of CN heterocyclic. The intense band at 807 cm⁻¹ represented the out of plane breathing vibration characteristic of triazine unites.^{37,38} And the peak at 3430 cm⁻¹ was attributed to the existence of water. For the BiVO₄/g- C_3N_4 composites, the peak intensities of ν_3 (VO₄) and ν_1 (VO₄) increased slightly with the increase of BiVO₄ content, indicating the co-existence of g- C_3N_4 and BiVO₄ in the composites.

The morphology of g- C_3N_4 , BiVO₄ and 3:7 BiVO₄/g- C_3N_4 were investigated by SEM. From Fig. S1a, a structure with several stacking layers could be clearly seen in the g- C_3N_4 sample, which was in line with the literature reports.^{39,40} The BiVO₄ sample displayed a plate-like structure with a diameter of 50 ~ 200 nm and a thickness of 10 ~ 30 nm (Fig. S1b). Fig. S1c revealed that the two types of materials were all found in the sample of BiVO₄/g- C_3N_4 with the molar ratio of 3:7. In addition, it was observed that quantities of BiVO₄ nanoparticles were clustered on or covered by the g- C_3N_4 nanosheets. In addition, the EDS profile in Fig. S1d and e clearly verified the presence of Bi, V, O, C, N elements in the 3:7 BiVO₄/g- C_3N_4 composite. The signal of Au was due to the gilding process.

The microstructure of g- C_3N_4 , BiVO₄ and 3:7 BiVO₄/g- C_3N_4 were further investigated by TEM and HRTEM. Clearly, the two-dimensional layered structure of the pure g- C_3N_4 can be seen from Fig. 2a. Based on the crystal structure of g- C_3N_4 from theoretical and previously experimental work, it might be inferred that the top surface of the layer is the (002) facet of g- C_3N_4 ²³ as presented in Fig. 2d. As shown in Fig. 2b, the pure BiVO₄ shows a number of plate-like nanostructures with a thickness of 10 ~ 30 nm. Also, Fig. 2b and HRTEM (Fig. 2e) proved that the top surface of BiVO₄ is (121) facet. Fig. 2c displayed the two type of nanosheets attached to each other with (002) facets of g- C_3N_4 and (121) facets of BiVO₄, indicating that the coupling between g- C_3N_4 and BiVO₄ may happen on the (002) facets of g- C_3N_4 and (121) facets of BiVO₄.

The XPS was employed to evaluate the surface chemical composition and the oxidation state of BiVO₄/g- C_3N_4 composites and to further study the interaction of g- C_3N_4 with BiVO₄. The overall XPS spectrum for the 3:7 BiVO₄/g- C_3N_4 was displayed in Fig. 3a, in which the Bi, O, V, C and N elements could all be investigated. Fig. 3b-f showed the high resolution spectra of Bi 4f, V 2p, O 1s, C 1s and N 1s for 3:7 BiVO₄/g- C_3N_4 composites, respectively. As shown in Fig. 3b, the binding energy values of Bi 4f_{7/2} and Bi 4f_{5/2} were observed at 164.4 eV and 159.1 eV, respectively. The high-resolution XPS spectra of 3:7 BiVO₄/g- C_3N_4 in Fig. 3c showed a peak at 529.5 eV, which can be attributed to V 2p. Obviously, two peaks can be detected in the high-resolution XPS spectra of O 1s region (Fig. 3d). And the main peak at 529.7 eV is assigned to the Bi-O bonds of (Bi₂O₂)²⁺ slabs in the layered structure of BiVO₄, while the peak at 530.7 eV is ascribed to the hydroxyl groups on the surface.⁴⁰ In Fig. 3e, the peak of C 1s at 284.6 eV is the characteristic of the

adventitious carbon on the surface of g-C₃N₄ and the peaks at 286 eV and 288.2 eV were both attributed to the sp² hybridized C (C-(N)₃).¹⁰ The main features of N 1s are shown in Fig. 3f and a broad and wide peak (397 ~ 403 eV) can be seen. The existence of sp²-bonded g-C₃N₄ in the BiVO₄/g-C₃N₄ composites could be verified by the N 1s peak at 398.8 eV reflecting the sp²-hybridized nitrogen (C=N-C).⁴¹ The two peaks observed at 400.1 eV and 401.3 eV were assigned to tertiary nitrogen (N-(C₃)) groups and the effects of charging reaction, respectively.⁴² The XPS results further demonstrated that the BiVO₄/g-C₃N₄ composite was successfully obtained.

The UV-vis DRS of the composites were displayed in Fig. 4, from which the optical absorption edges of the pure g-C₃N₄ and BiVO₄ were approximately estimated from the absorption onsets to be 450 and 525 nm, respectively. After the combination of g-C₃N₄ and BiVO₄, the absorption band edges of the composites gradually shift toward that of pure BiVO₄ with the increase of BiVO₄ content, which reveals that BiVO₄ is a good and apposite visible-light sensitizer to g-C₃N₄. The band gap (E_g) can be determined by the formula.⁴³

$$\alpha h\nu = A (h\nu - E_g)^{n/2} \quad (1)$$

Where α , h , m , E_g and A are absorption coefficient, Planck constant, light frequency, band gap energy, and a constant, respectively. Among them, n is determined by the type of optical transition of a semiconductor ($n = 1$ for direct transition and $n = 4$ for indirect transition).^{44,45} As the previous literature reported, the n value of g-C₃N₄ was 4, and the n value of BiVO₄ was 1. From the plot of $(\alpha h\nu)^{1/2}$ or $(\alpha h\nu)^2$ versus $(h\nu)$ in Fig. 4a and Fig. 4b, the E_g of g-C₃N₄ and BiVO₄ were estimated to be 2.60 eV and 2.45 eV, respectively. Meanwhile, the E_g of BiVO₄/g-C₃N₄ heterostructures were similar to that of pure BiVO₄.

3.2. Photocatalytic activity

The photocatalytic activity of the BiVO₄/g-C₃N₄ composite photocatalysts as well as pure BiVO₄ and C₃N₄ were examined by degradation of RhB molecules under visible-light irradiation ($\lambda > 420$ nm). Fig. 5a shows the photocatalytic degradation curves of RhB with the as-obtained photocatalysts under visible-light illumination for 5 h. It can be seen clearly that both the pristine g-C₃N₄ and BiVO₄ display relatively poor visible-light-induced degradation efficiency. When the molar ratio of BiVO₄ to g-C₃N₄ in the composites was 3:7, the highest degradation efficiency of 85% was observed within 5 h. The pseudo-first-order kinetic curves of RhB photodegradation were also plotted to analyze the degradation rate quantitatively. The experimental data clearly displayed that the apparent rate constant k is 0.033 h⁻¹, 0.032 h⁻¹, 0.066 h⁻¹, 0.139 h⁻¹, 0.342 h⁻¹, 0.041h⁻¹, and 0.049h⁻¹ for the pristine g-C₃N₄, BiVO₄ and BiVO₄/g-C₃N₄ composites with molar ratios of 1:9, 2:8, 3:7, 4:6, 5:5, respectively (Fig. 5c). In other words, the photocatalytic activity of 3:7 BiVO₄/g-C₃N₄ is 10.36 and 10.68 times higher than those of single g-C₃N₄ and BiVO₄, respectively. From Fig. 5b, the maximum absorbance of the solution shifted from 554 to 530 nm after 5 h irradiation, indicating that the N-demethylation and de-ethylation reactions happened during the photodegradation process.^{46,47} For the purpose of verifying the active species during the photocatalytic reaction and determining the corresponding photocatalytic mechanism, tert-butyl alcohol (TBA), disodium

ethylenediaminetetraacetate (EDTA) and 1, 4-benzoquinone (BQ) were employed as the hydroxyl radical (\bullet OH) scavenger, hole (h^+) scavenger and superoxide radical (\bullet O₂⁻) scavenger,²⁷ respectively. When EDTA was added to the solution, the RhB degradation rate for the 3:7 BiVO₄/g-C₃N₄ composite is slightly depressed as depicted in Fig. 5d, revealing that only a small amount of the holes were participated in the RhB degradation processes. However, the decrease of degradation rate is obviously observed with the addition of 1 mM of tertbutyl alcohol (TBA), which acted as a scavenger for \bullet OH radical species. In addition, the degradation of RhB was also significantly depressed with adding 1 mM of \bullet O₂⁻ scavenger BQ, indicating that the \bullet O₂⁻ also play a vital role during the RhB oxidation process. Thus, the active species trapping experiments demonstrated that the \bullet O₂⁻ and \bullet OH are the two main active species in the degradation process of RhB. For the sake of comparison, the influences of additions (EDTA, TBA and BQ) toward the photocatalytic activity over both pure BiVO₄ and g-C₃N₄ were also investigated as illustrated in Fig. S2. From Fig. S2, we can conclude that \bullet O₂⁻ plays the most crucial role in the oxidation process of RhB over pure g-C₃N₄. While for the pure BiVO₄, h^+ was the main active species in the RhB degradation process. Comparatively, as depicted in the Fig. 5d, the main active species of 3:7 BiVO₄/g-C₃N₄ sample in the degradation process of RhB are \bullet O₂⁻ and \bullet OH, which was in agreement with the principle of Z-scheme photocatalytic mechanism. The BET specific surface area of 3:7 BiVO₄/g-C₃N₄ composite is 4.52 m²/g, which is a little higher than bulk g-C₃N₄ (4.01 m²/g), indicating that the slightly increased specific surface area is not the main reason for the highly enhanced photocatalytic activity of BiVO₄/g-C₃N₄ composite.

3.3. Mechanism investigation on the enhanced photocatalytic activity

The conduction band (CB) and valence band (VB) potentials of g-C₃N₄ and BiVO₄ can be calculated by the following equations:⁴⁸

$$E_{VB} = X - E_e + 0.5E_g \quad (2)$$

$$E_{CB} = E_{VB} - E_g \quad (3)$$

where E_{VB} is the VB edge potential; X is the electronegativity of the semiconductor, which is the geometric average of the absolute electronegativity of the constituent atoms (X values of g-C₃N₄ and BiVO₄ are 4.67eV and 6.16eV, respectively); E_e is the energy of free electrons on the hydrogen scale ($E_e \approx 4.5$ eV),⁴⁹ and E_g is the band gap energy of the semiconductor. The band gap energies of g-C₃N₄ and BiVO₄ are adopted as 2.60 eV and 2.45 eV, respectively. The positions of the conduction and the valence bands of g-C₃N₄ and BiVO₄ calculated by Eq. (2) and (3) were listed in Table S1 (Supporting Information).

Fig. 6a depicts the crystal structure of BiVO₄, which is a typical scheelite compound. Its crystal structure is composed of alternating (Bi₂O₂)²⁺ slabs and (VO₄)²⁻ octahedral layers. This layered configuration is considered to enhance the separation of electron-hole pairs and decrease the recombination rate of the charge carriers. The (121) facet of BiVO₄ was figuratively marked in the Fig. 6a. The two types of nanosheets attached to

each other with (002) facets of g-C₃N₄ and (121) facets of BiVO₄. Thus, we can deem that the coupled structure between g-C₃N₄ and BiVO₄ will benefit for the separation of electron-hole pairs, so as to contribute to the enhancement of photodegradation on RhB under visible-light irradiation. The possible separation and transfer mechanism of the photoexcited charge carriers was proposed as depicted in Fig. 6c. Because the gap (1.56eV) between the CB of g-C₃N₄ and the CB of BiVO₄ is much larger than that (1.04eV) between the CB of BiVO₄ and the VB of g-C₃N₄, the photoexcited electrons in the CB of BiVO₄ transfer to the VB of g-C₃N₄ quickly, leading to the combination of electrons in the CB of BiVO₄ and photogenerated holes in the VB of g-C₃N₄. It accumulated rich electrons in the CB of g-C₃N₄ and holes in the VB of BiVO₄ to involve in the redox reactions. Consequently, the more negative potentiated electrons in the CB of g-C₃N₄ reduce the molecular oxygen to yield •O₂⁻, and then induces the RhB degradation. Meanwhile, the more positive potentiated holes in the VB of BiVO₄ produce rich active •OH radicals with powerful oxidization. Hence the photocatalytic activity of BiVO₄/g-C₃N₄ composites were significantly promoted, and RhB is photodegraded via •O₂⁻, •OH or direct h⁺ oxidation pathway. Based on the above results, the BiVO₄/g-C₃N₄ system is a type of direct Z-scheme photocatalyst.

In order to prove the mechanism responsible for the remarkably improved visible-light induced photocatalysis, we conducted a series of tests such as photoluminescence spectra (PL), photocurrent-time measurement and electrochemical impedance spectroscopy (EIS).⁵⁰⁻⁵² PL emission are mainly originated from the recombination of the photoexcited electrons and holes in semiconductors. And PL intensity has a strong correlation with photocatalytic activity of a photocatalyst. Generally, lower PL intensity reveals lower recombination rate of electron-hole pairs, thus higher photocatalytic performance.^{26,53} In order to analyze the recombination of the charge carriers generated from g-C₃N₄, BiVO₄, and 3:7 BiVO₄/g-C₃N₄, the PL spectra with excitation wavelength 254 nm were measured and depicted in Fig. 7. The main emission peak centred on 460 nm for the g-C₃N₄ sample could be attributed to the band gap recombination of charge carries. In comparison with g-C₃N₄, combining with BiVO₄ does not affect the spectral position of the peaks, but reduces the relative intensity of PL spectra (inset of the Fig. 7). These results indicated that the mediator-free direct Z-scheme photocatalytic system of BiVO₄/g-C₃N₄ dedicates to the effective charge separation, thus creating a significantly improved photocatalytic activity for the BiVO₄/g-C₃N₄ composites under visible-light irradiation.

The photocurrent-time measurement was employed to evaluate the interfacial charge transfer dynamics between the g-C₃N₄ and BiVO₄. Fig. 8a displays the transient photocurrent responses produced by the pure g-C₃N₄, BiVO₄ and 3:7 BiVO₄/g-C₃N₄ samples. The photocurrent intensity remained at a relatively high constant value when the light was on and rapidly decreased to zero as long as the light was turned off. Obviously, the photocurrent over 3:7 BiVO₄/g-C₃N₄ composite is greatly improved, which is about 2 and 3 times as those of BiVO₄ and g-C₃N₄, respectively. The higher photocurrent demonstrates the higher efficiency of charge separation.^{27,54} The results of

photocurrent-time measurement suggested that the 3:7 BiVO₄/g-C₃N₄ heterostructure possesses more powerful ability in charge separation than the pristine g-C₃N₄ and BiVO₄. EIS measurement was employed to detect the charge transfer processes at solid/electrolyte interfaces. The radius of the arc on the EIS spectra implies the interface layer resistance happened on the surface of electrode. The smaller arc radius indicates the higher efficiency of charge transfer.^{26,27,46} As shown in Fig. 8b, the diameter of the arc radius on the EIS Nyquist plot of the 3:7 BiVO₄/g-C₃N₄ composite electrode is much smaller than that of the pure BiVO₄ electrode, suggesting a more effective separation of photoexcited charge carries and rapid interfacial charge transfer occurred in the 3:7 BiVO₄/g-C₃N₄ composites.

To further confirm the Z-scheme mechanism and examine that the •O₂⁻ and •OH radicals mainly conduce to the degradation of RhB molecules over 3:7 BiVO₄/g-C₃N₄ under visible light irradiation ($\lambda > 420$ nm). Quantification experiments of •O₂⁻ production were performed thorough the transformation of NBT (detection agent of •O₂⁻) during the photocatalytic reaction.²³ Fig. 9 showed the spectra of the transformation percentage of NBT. For pure g-C₃N₄, the CB potential of g-C₃N₄ (-1.13 eV vs NHE) is more negative than E₀(O₂/•O₂⁻ = -0.046 eV vs NHE). Thus, g-C₃N₄ shows obvious transformation percentage of NBT (Fig. 9a), while that for pure BiVO₄ (Fig. 9b) can be neglected. It can be concluded that there are almost no •O₂⁻ produced from the electrons of BiVO₄, because its CB potential (0.43 eV vs NHE) is more positive than E₀(O₂/•O₂⁻ = -0.046 eV vs NHE), and the standard redox potential of Bi⁴⁺/Bi³⁺ (1.59 eV) is more negative than that of •OH/OH⁻ (+1.99 eV).²⁷ After the combination of g-C₃N₄ and BiVO₄, most of electrons in the CB of BiVO₄ were transferred to the VB of g-C₃N₄ and recombined with the holes there according to the above energy potentials analysis (Fig. 6), which enables the electrons remained in the CB of g-C₃N₄ to react with O₂ to generate more •O₂⁻. It was proved by the highest transformation percentage of NBT of BiVO₄/g-C₃N₄ as shown in Fig. 9c. Moreover, the NBT transformation percentage of the 3:7 BiVO₄/g-C₃N₄ composite is also higher than that of the mechanically mixed sample (Fig. 9d). These results demonstrate that the photogenerated electrons on the CB of BiVO₄ could easily transfer to the VB of g-C₃N₄, resulting in more effective charge separation and reducing the probability of recombination of electron-hole pairs in the BiVO₄/g-C₃N₄ composites. Especially, the 3:7 BiVO₄/g-C₃N₄ holds more g-C₃N₄, leading to that more photogenerated electrons can react with O₂ to produce •O₂⁻ and take part in decomposition of RhB, which is in good agreement with the active species trapping experiments (Fig 5d).

Furthermore, the terephthalic acid photoluminescence probing technique (TA-PL) was also applied to investigate the •OH radicals since TA could react with •OH radicals to form a highly fluorescent 2-hydroxyterephthalic acid (TAOH).^{30,50} For pure BiVO₄, there is almost no •OH species generated because of the rapid decay through recombination of photoexcited charge carries (Fig. 10b). Compared with pure g-C₃N₄ (Fig. 10a) and BiVO₄ (Fig. 10b), the highest PL intensity was observed over the 3:7 BiVO₄/g-C₃N₄ composite as shown in Fig. 10c. This should be attributed to the Z-scheme charge transfer,^{27,29} which results in the enrichment of holes on the VB of BiVO₄ to produce more

•OH, resulting in the highest PL peak of BiVO₄/g-C₃N₄ composite. In addition, the PL intensities of BiVO₄/g-C₃N₄ composite at approximately 425 nm at different times in Fig. 10c were also obviously higher than that of the mechanically mixed sample (Fig. 10d), confirming the successful construction of BiVO₄/g-C₃N₄ composite with efficient charge transfer. Based on the results of NBT transformation and TA-PL results, the photodecomposition of RhB over BiVO₄/g-C₃N₄ is truly according to a Z-scheme reaction mechanism.

4. Conclusions

A mediator-free direct Z-scheme photocatalyst BiVO₄/g-C₃N₄ was synthesized via a mixed-calcinations route. The coupling between g-C₃N₄ and BiVO₄ happens on the (002) and (121) facets of g-C₃N₄ and BiVO₄, respectively. All the as-synthesized BiVO₄/g-C₃N₄ composites exhibited more excellent photocatalytic performance than the individuals under visible-light irradiation. The detailed active species trapping and quantification experiments of •O₂⁻ and •OH production over BiVO₄/g-C₃N₄ composites and the individuals revealed that the significantly improved photocatalytic activity should be attributed to the fabrication of Z-scheme principled BiVO₄/g-C₃N₄, which can result in the more efficient separation and largely reduced recombination probability of photoexcited electron-hole pairs, thus enabling highly powerful oxidation and reduction capability. It was also verified by the PL spectra and photoelectrochemical experiments.

Acknowledgement

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Notes and references

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† Electronic Supplementary Information (ESI) available: Absolute electronegativity, energy band gap, calculated conduction band edge position and valence band edge position of g-C₃N₄ and BiVO₄ semiconductors. SEM images of the g-C₃N₄, BiVO₄ and 3:7 BiVO₄/g-C₃N₄ samples. Photocatalytic degradation curves of RhB over g-C₃N₄ and BiVO₄ alone and with the addition of TBA, EDTA, or BQ. See DOI:10.1039/b000000x

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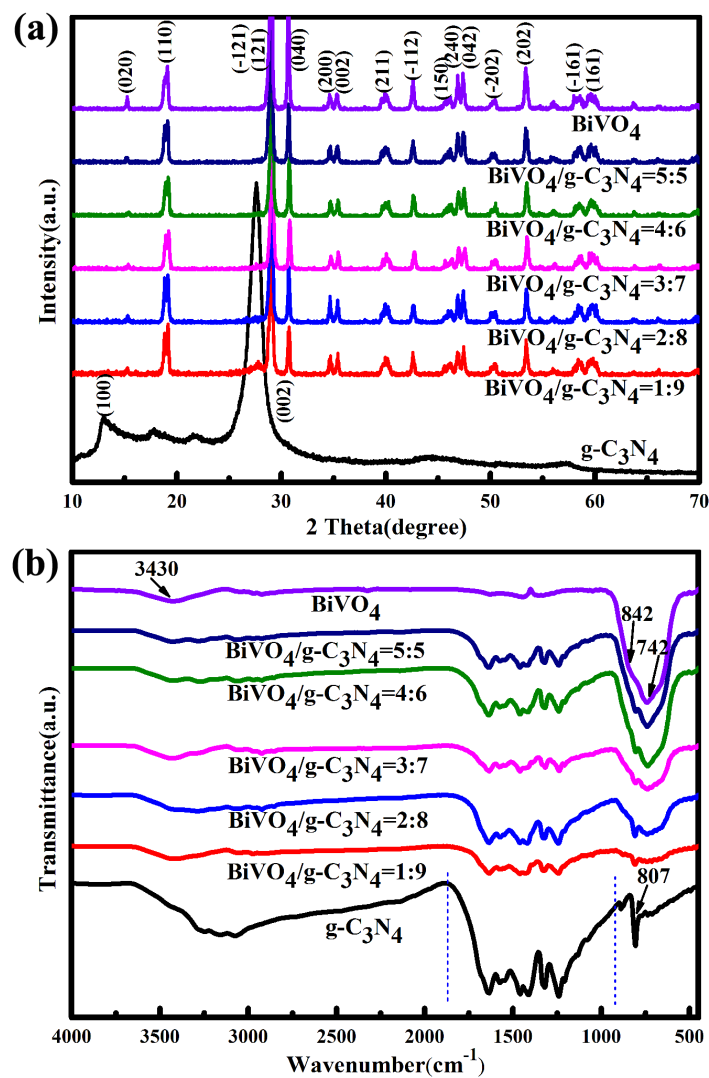


Fig. 1 (a) XRD patterns and (b) FTIR spectra of $\text{g-C}_3\text{N}_4$, BiVO_4 and $\text{BiVO}_4/\text{g-C}_3\text{N}_4$ composites with molar ratios of 1:9, 2:8, 3:7, 4:6 and 5:5.

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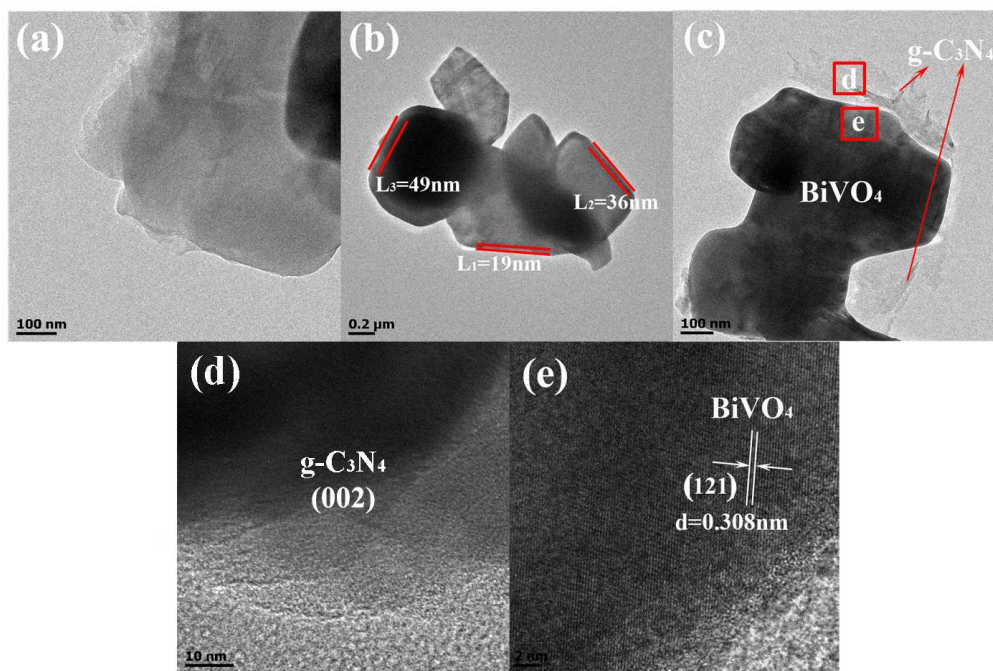


Fig. 2 TEM images of the as-obtained samples: (a) g-C₃N₄, (b) BiVO₄, (c) 3:7 BiVO₄/g-C₃N₄;

HRTEM images of (d, e) 3:7 BiVO₄/g-C₃N₄.

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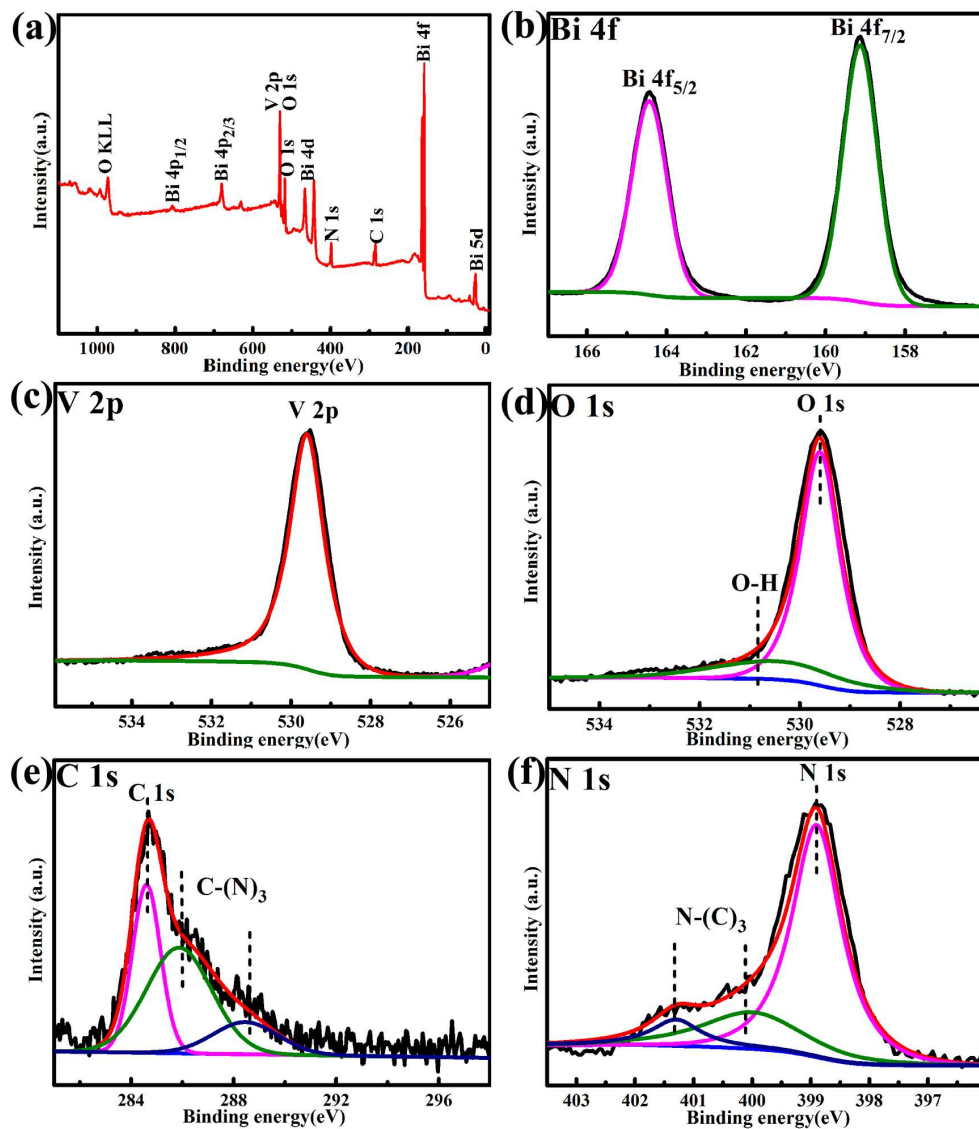


Fig. 3 (a) Typical XPS survey spectra of 3:7 BiVO₄/g-C₃N₄. High resolution XPS spectra of (b) Bi 4f,

(c) V 2p, (d) O 1s, (e) C 1s, and (f) N 1s of 3:7 BiVO₄/g-C₃N₄.

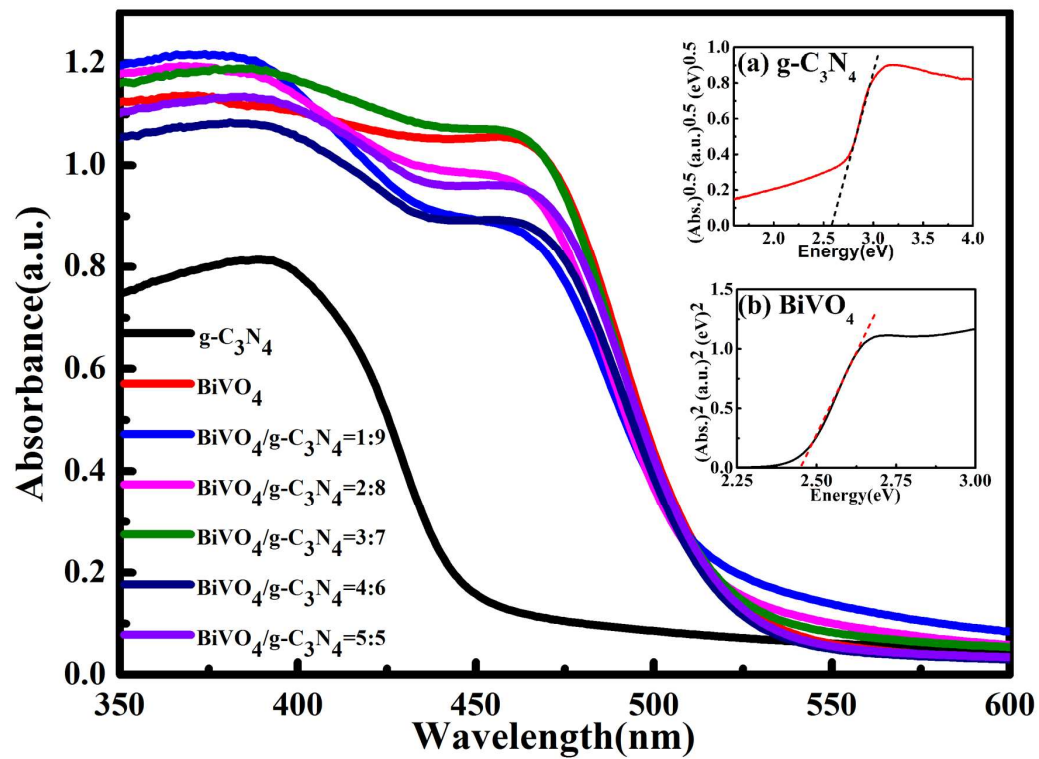


Fig. 4 UV-vis diffuse reflectance spectra of $g\text{-C}_3\text{N}_4$, BiVO_4 , $\text{BiVO}_4/g\text{-C}_3\text{N}_4$ composites with molar ratios of 1:9, 2:8, 3:7, 4:6 and 5:5.

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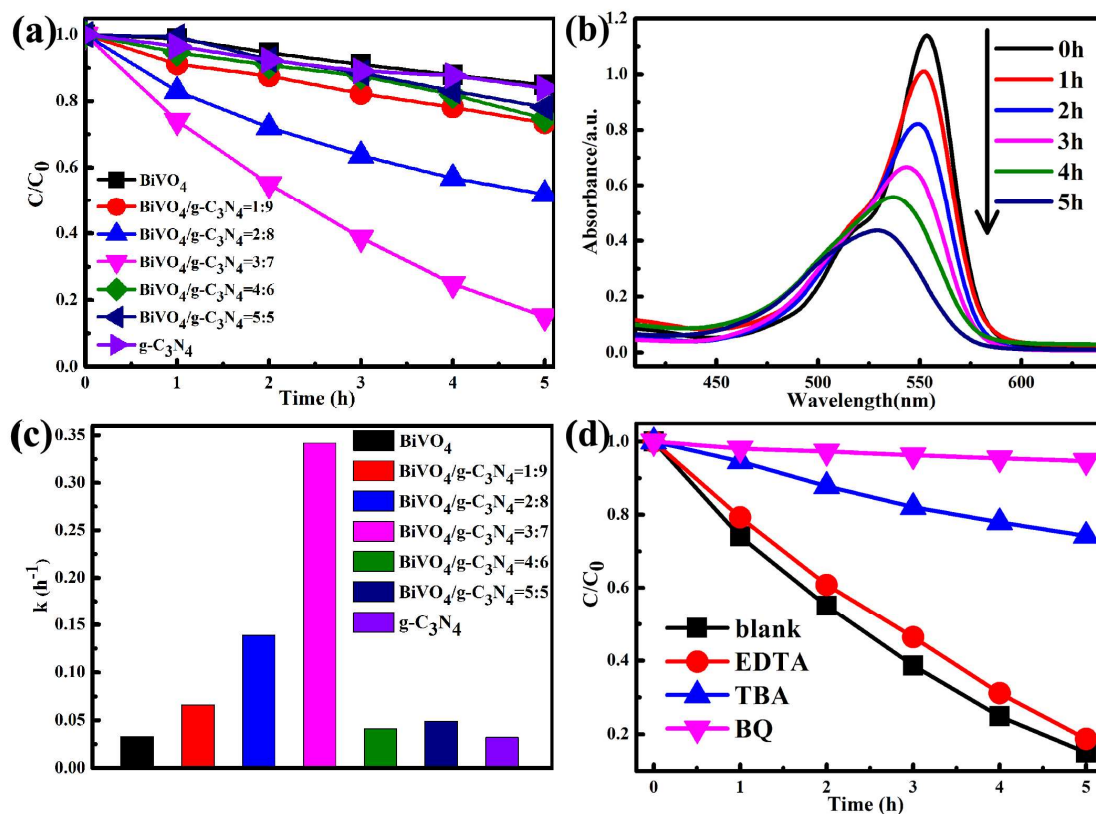


Fig. 5 (a) Photocatalytic degradation curves of RhB over as-prepared BiVO₄/g-C₃N₄ samples under the visible light irradiation ($\lambda > 420$ nm); (b) UV-visible spectra of RhB at different visible-irradiation-times in the presence of 3:7 BiVO₄/g-C₃N₄; (c) Apparent rate constants for the photodegradation of RhB over BiVO₄/g-C₃N₄ under visible light irradiation ($\lambda > 420$ nm); (d) Photocatalytic degradation of RhB over 3:7 BiVO₄/g-C₃N₄ photocatalysts alone and with the addition of TBA, EDTA, or BQ.

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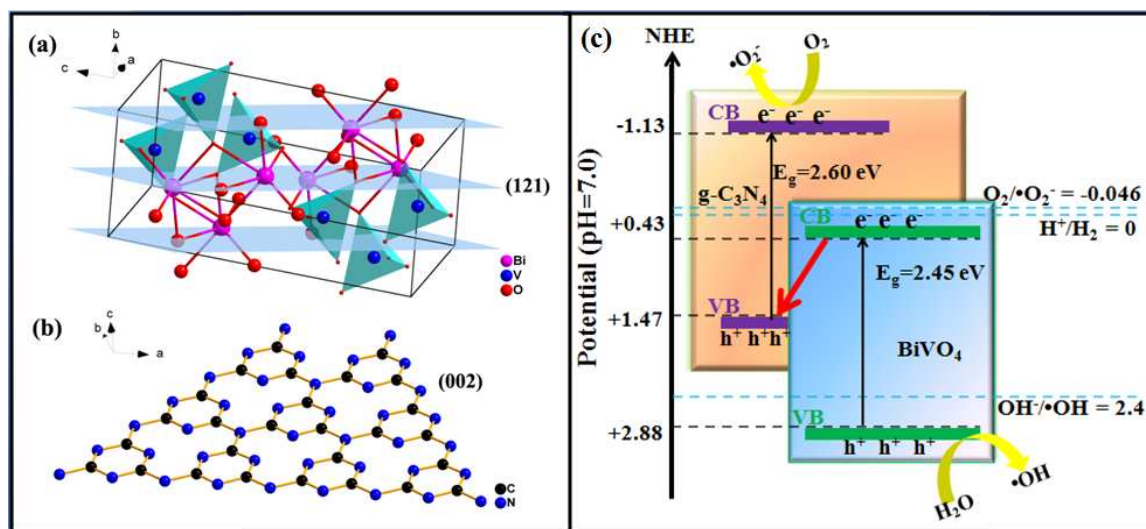


Fig. 6 Crystal structure of (a) BiVO₄ and (b) g-C₃N₄; (c) Schematic diagrams for interfacial charge transfer of BiVO₄/g-C₃N₄ Z-scheme photocatalyst.

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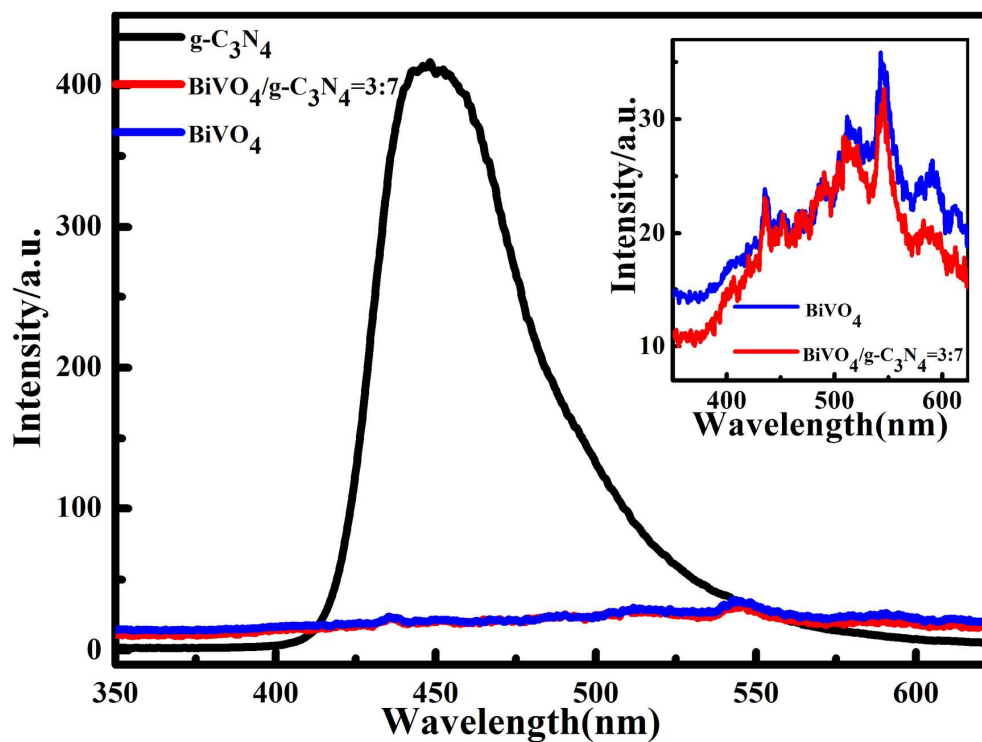


Fig. 7 Photoluminescence spectra of g-C₃N₄, BiVO₄, and 3:7 BiVO₄/g-C₃N₄ photocatalysts.

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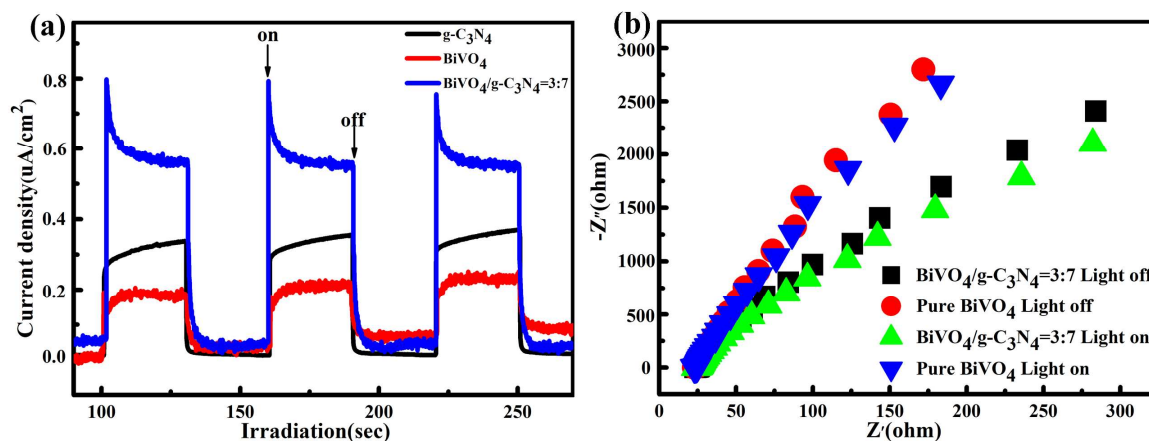


Fig. 8 (a) Comparison of transient photocurrent responses of the g-C₃N₄, BiVO₄ and 3:7 BiVO₄/g-C₃N₄ and (b) EIS Nyquist plots of the g-C₃N₄ and 3:7 BiVO₄/g-C₃N₄ with light on/off cycles under visible light irradiation ($\lambda > 420$ nm, [Na₂SO₄] = 0.1 M).

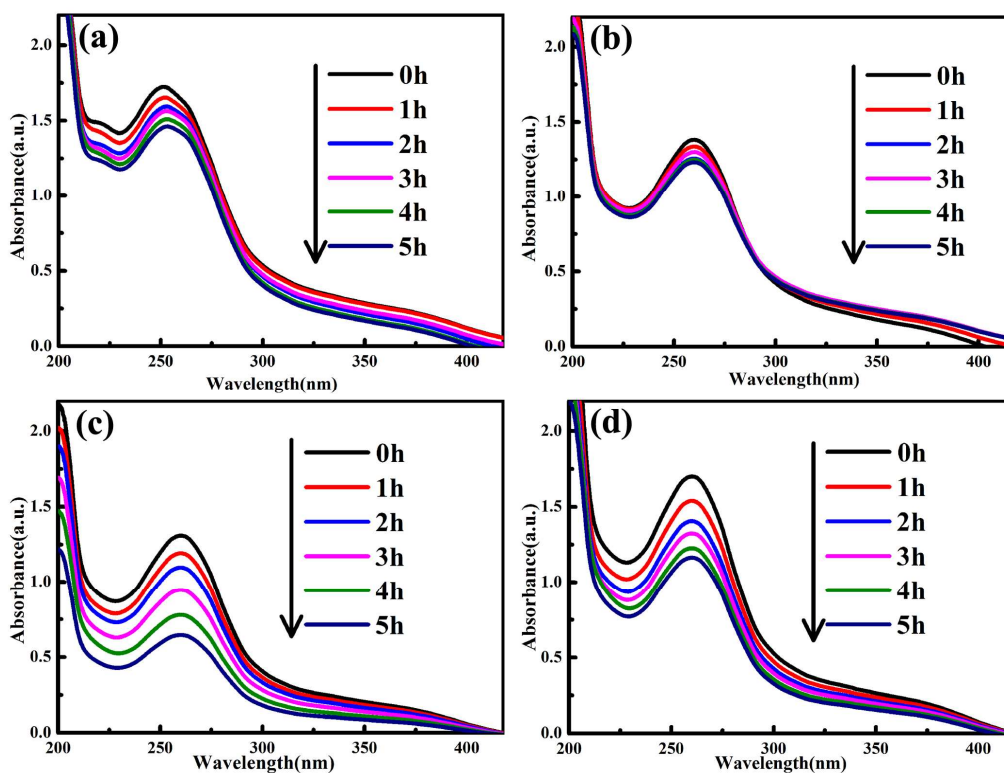


Fig. 9 Spectra of NBT transformation generated by (a) 50mg of $g\text{-C}_3\text{N}_4$, (b) 50mg of BiVO_4 , (c) 50mg of 3:7 $\text{BiVO}_4/g\text{-C}_3\text{N}_4$ and (d) mechanically mixed 35mg $g\text{-C}_3\text{N}_4$ with 15mg BiVO_4 under irradiation with visible light ($\lambda > 420$ nm).

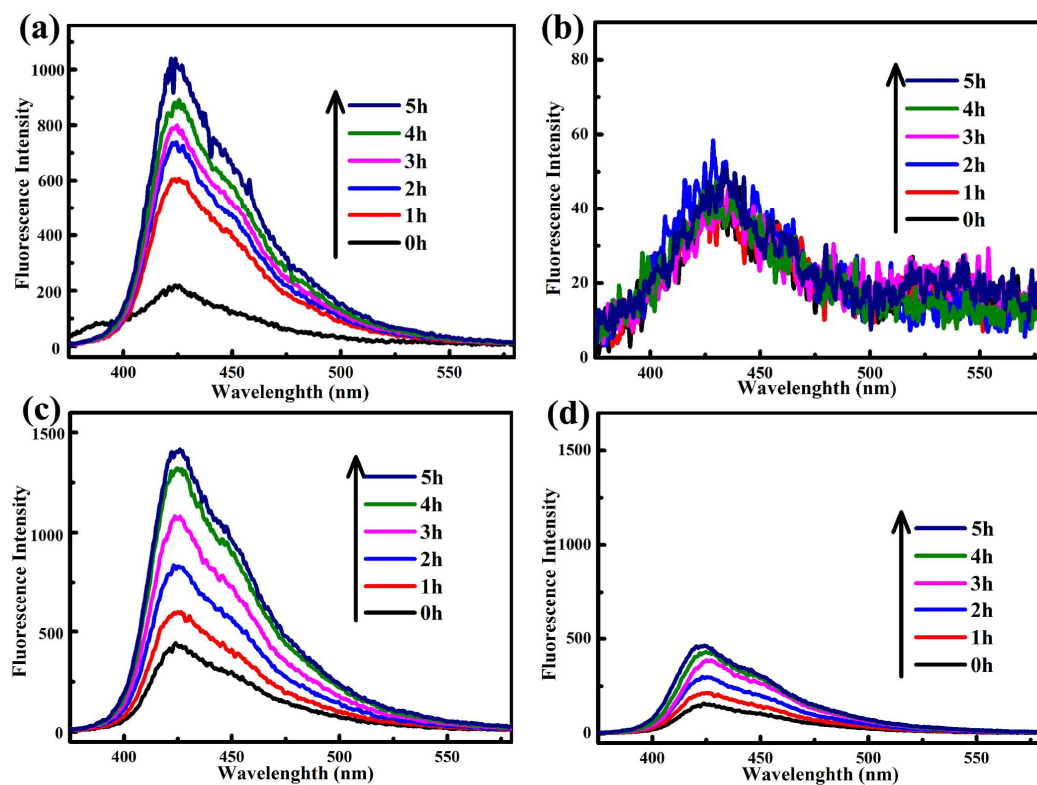


Fig. 10 Fluorescence spectra of a TAOH solution generated by (a) 50mg of $g\text{-C}_3\text{N}_4$, (b) 50mg of BiVO_4 , (c) 50mg of 3:7 $\text{BiVO}_4/g\text{-C}_3\text{N}_4$ and (d) mechanically mixed 35mg $g\text{-C}_3\text{N}_4$ with 15mg BiVO_4 under irradiation with visible light ($\lambda > 420 \text{ nm}$)

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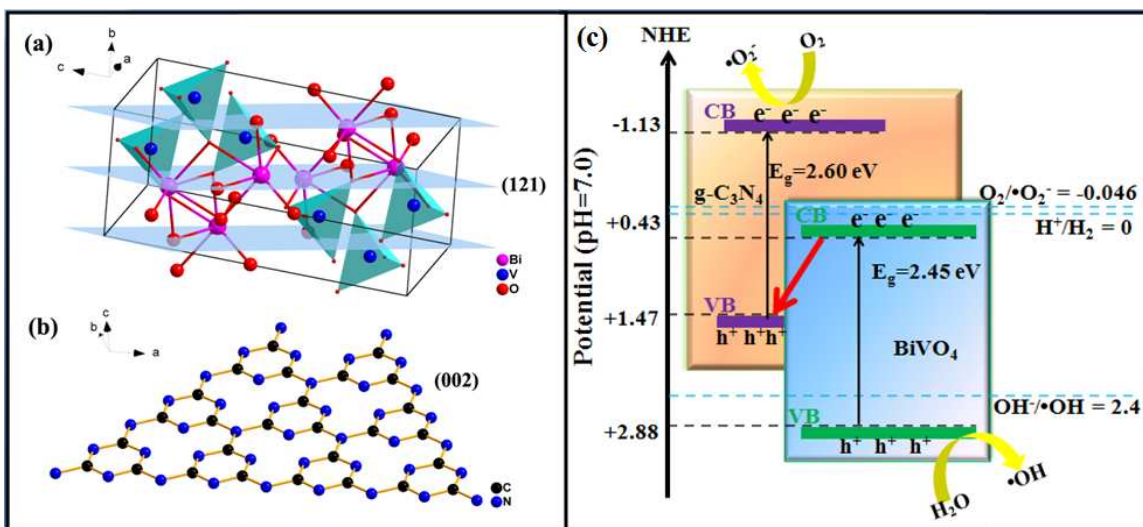
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Mediator-free direct Z-scheme photocatalytic system: $\text{BiVO}_4/\text{g-C}_3\text{N}_4$ organic-inorganic hybrid photocatalyst with highly efficient visible-light-induced photocatalytic activity

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Mediator-free Z-scheme $\text{BiVO}_4/\text{g-C}_3\text{N}_4$ photocatalysts were successfully obtained based on band gap engineering design. It exhibits high visible-light-driven photocatalytic activity for degradation of RhB and photocurrent generation. The much more powerful oxidation and reduction capability of the samples were demonstrated by the active species experiments, NBT transformation and TA-PL probing technique.